

MAXIMUM RATINGS (T_J = 25° C unless otherwise noted)

l l	Symbol	Value	Unit		
Drain-to-Source Voltage Internally Clamped		V _{DSS}	60	Vdc	
Gate-to-Source Voltage		V _{GS}	±14	Vdc	
Drain Current	Continuous	۱ _D	9 s24Limi432.661 .9071 re8 0 0 8 74.9		e8 0 0 8 74.929

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit

TYPICAL PERFORMANCE CURVES

TYPICAL PERFORMANCE CURVES



Figure 9. R_{DS(on)} vs. Drain Current

TEST CIRCUITS AND WAVEFORMS

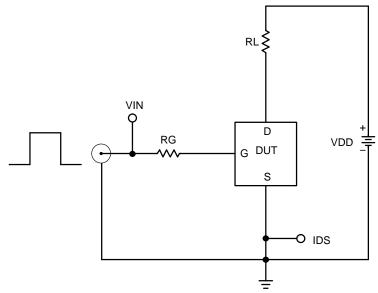


Figure 23. Resistive Load Switching Test Circuit

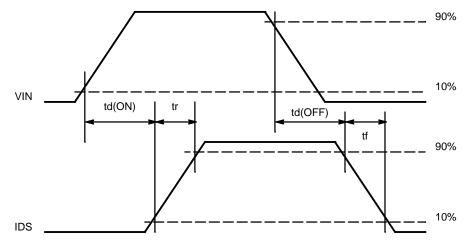
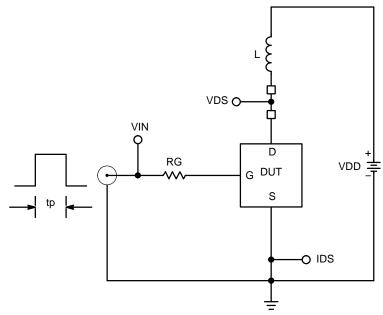
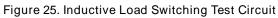
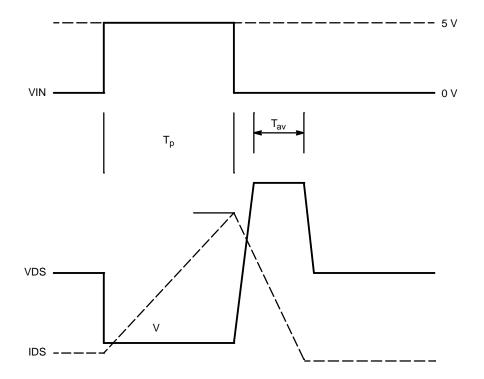


Figure 24. Resistive Load Switching Waveforms

TEST CIRCUITS AND WAVEFORMS







ORDERING INFORMATION

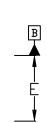
Device

Package

Shipping

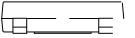


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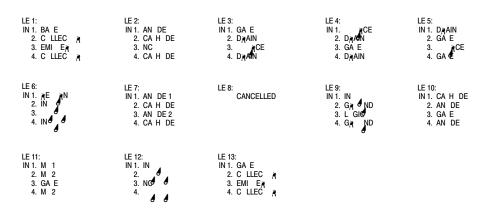
	MILLIMETERS				
DIM	MIN.	NDM.	MAX.		
A	1.50	1.63	1.75		
A1	0.02	0.06	0.10		
b					
D	6.30	6.50	6.70		
E	3.30	3.50	3.70		
e	i	2.30 BSC	;		

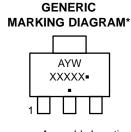
2





DATE 02 OCT 2018





- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb Free Package
- (Note: Microdot may be in either location) *This information is generic. Please refer to device data sheet for actual part marking. Pb Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT-223 (TO-261)		PAGE 2 OF 2	

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DATE 31 MAY 2023

STYLE 1: PIN 1. BASE 2. COLLE 3. EMITT 4. COLLE	ER 3. SO	AIN 2. CATH JRCE 3. ANOE	ODE 2. ANODE DE 3. GATE	STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE
STYLE 6:	STYLE 7:	3. ANODE	STYLE 9:	STYLE 10:
PIN 1. MT1	PIN 1. GATE		PIN 1. ANODE	PIN 1. CATHODE
2. MT2	2. COLLECTOF		2. CATHODE	2. ANODE
3. GATE	3. EMITTER		3. RESISTOR ADJUST	3. CATHODE
4. MT2	4. COLLECTOF		4. CATHODE	4. ANODE

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